

# BYV34G-600

Dual rectifier diode, ultrafast

Rev. 01 — 25 February 2009

Product data sheet

## 1. Product profile

### 1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT226 (I2PAK), low-profile plastic package.

### 1.2 Features

- Fast switching
- Soft recovery characteristic
- Low switching loss
- Low thermal resistance
- High thermal cycling performance
- Low forward voltage drop

### 1.3 Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

### 1.4 Quick reference data

- $V_{RRM} \leq 600 \text{ V}$
- $V_F \leq 1.16 \text{ V}$
- $I_{O(AV)} \leq 20 \text{ A}$
- $t_{rr} \leq 60 \text{ ns}$

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	anode 1		
2	cathode		
3	anode 2		
mb	mounting base; cathode		

SOT226 (I2PAK)

### 3. Ordering information

**Table 2. Ordering information**

Type number	Package		Version
	Name	Description	
BYV34G-600	I2PAK	plastic single-ended package (I2PAK); low-profile 3-lead TO-220AB	SOT226

### 4. Limiting values

**Table 3. Limiting values**

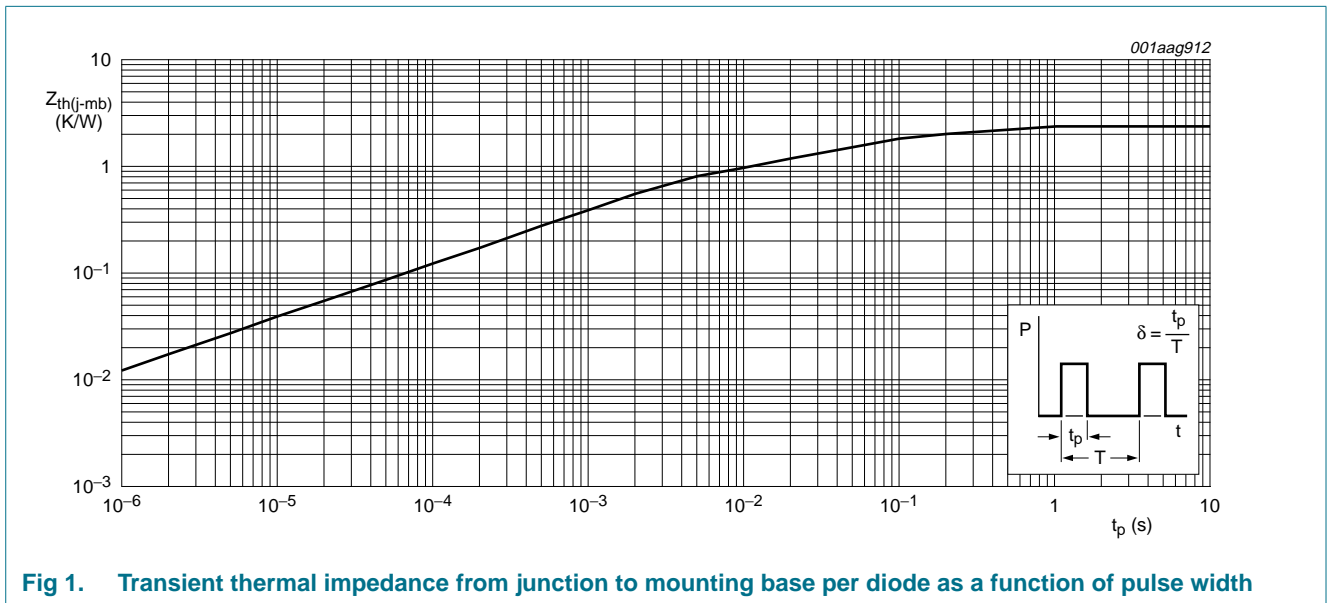
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC; $T_{mb} \leq 138\text{ °C}$	-	600	V
$I_{O(AV)}$	average output current	square waveform; $\delta = 0.5$ ; $T_{mb} \leq 107\text{ °C}$ ; both diodes conducting	-	20	A
$I_{FRM}$	repetitive peak forward current	$t_p = 25\ \mu\text{s}$ square waveform; $\delta = 0.5$ ; $T_{mb} \leq 107\text{ °C}$ ; per diode	-	20	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; sinusoidal waveform; per diode	-	120	A
		$t_p = 8.3\text{ ms}$ ; sinusoidal waveform; per diode	-	132	A
$T_{stg}$	storage temperature		-40	+150	°C
$T_j$	junction temperature		-	150	°C

**5. Thermal characteristics**

**Table 4. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound per diode; see <a href="#">Figure 1</a>	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

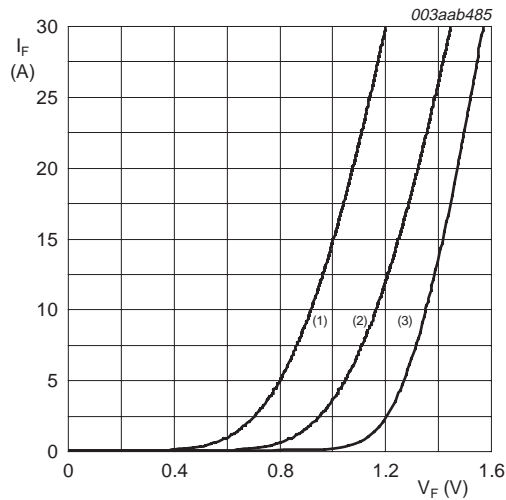


## 6. Characteristics

**Table 5. Characteristics**

$T_j = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 10\text{ A}$ ; $T_j = 150\text{ °C}$ ; see <a href="#">Figure 2</a>	-	0.92	1.16	V
		$I_F = 20\text{ A}$	-	1.07	1.48	V
$I_R$	reverse current	$V_R = 600\text{ V}$	-	10	50	$\mu\text{A}$
		$V_R = 600\text{ V}$ ; $T_j = 100\text{ °C}$	-	0.2	0.6	mA
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 2\text{ A}$ to $V_R = 30\text{ V}$ ; $di_F/dt = 20\text{ A}/\mu\text{s}$ ; see <a href="#">Figure 3</a>	-	40	70	nC
$t_{rr}$	reverse recovery time	$I_F = 1\text{ A}$ to $V_R = 30\text{ V}$ ; $di_F/dt = 100\text{ A}/\mu\text{s}$ ; ramp recovery; see <a href="#">Figure 3</a>	-	50	60	ns
$I_{RM}$	peak reverse recovery current	$I_F = 10\text{ A}$ to $V_R = 30\text{ V}$ ; $di_F/dt = 50\text{ A}/\mu\text{s}$ ; $T_j = 100\text{ °C}$ ; see <a href="#">Figure 3</a>	-	3	5	A
$V_{FR}$	forward recovery voltage	$I_F = 10\text{ A}$ ; $di_F/dt = 10\text{ A}/\mu\text{s}$ ; see <a href="#">Figure 4</a>	-	3.2	-	V



- (1)  $T_j = 150\text{ °C}$ ; typical values
- (2)  $T_j = 150\text{ °C}$ ; maximum values
- (3)  $T_j = 25\text{ °C}$ ; maximum values

**Fig 2. Forward current as a function of forward voltage**

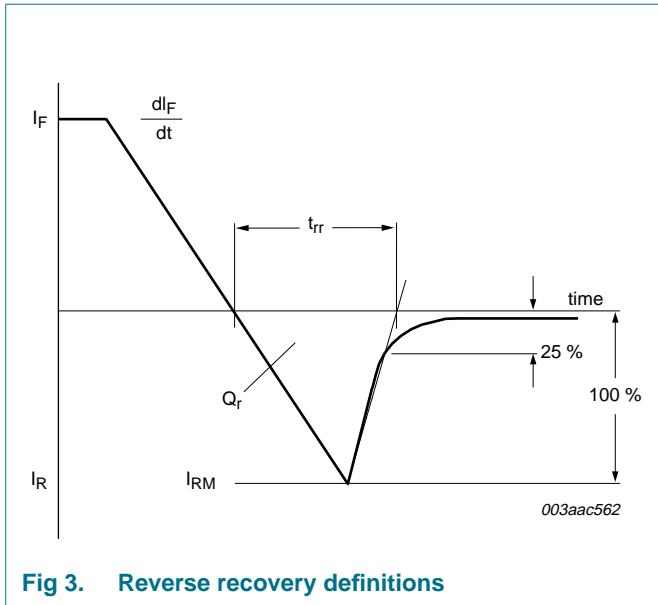


Fig 3. Reverse recovery definitions

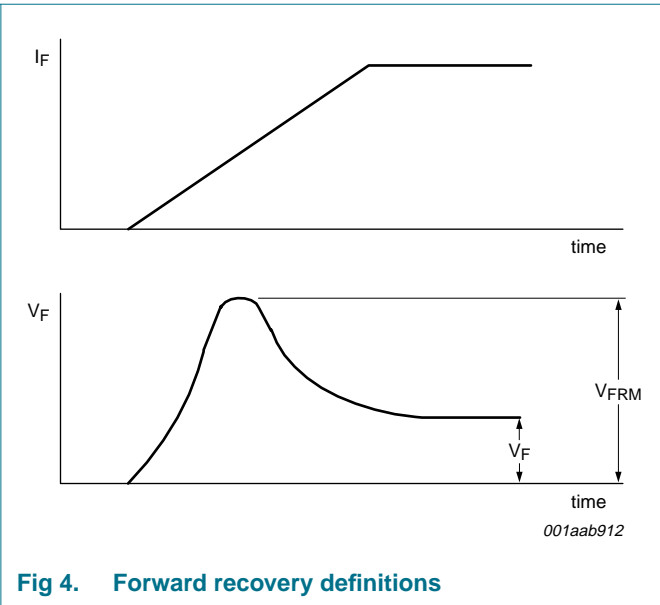


Fig 4. Forward recovery definitions

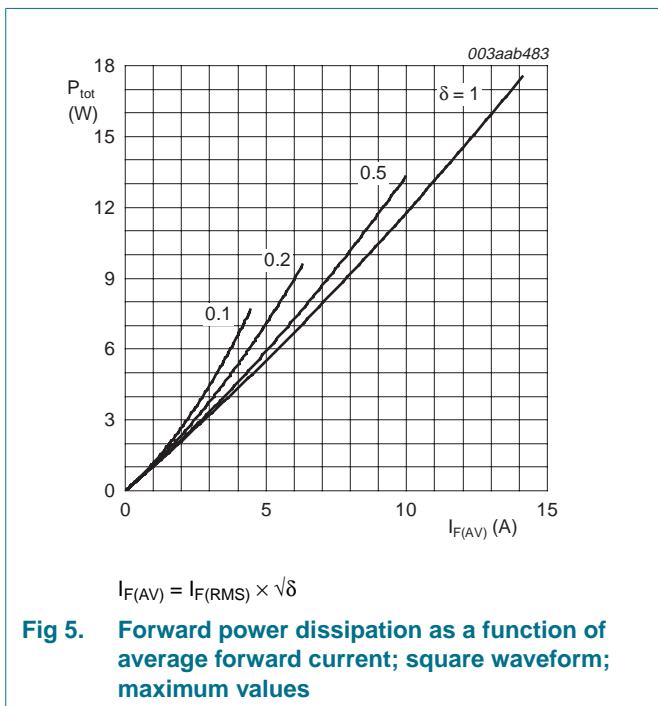


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values

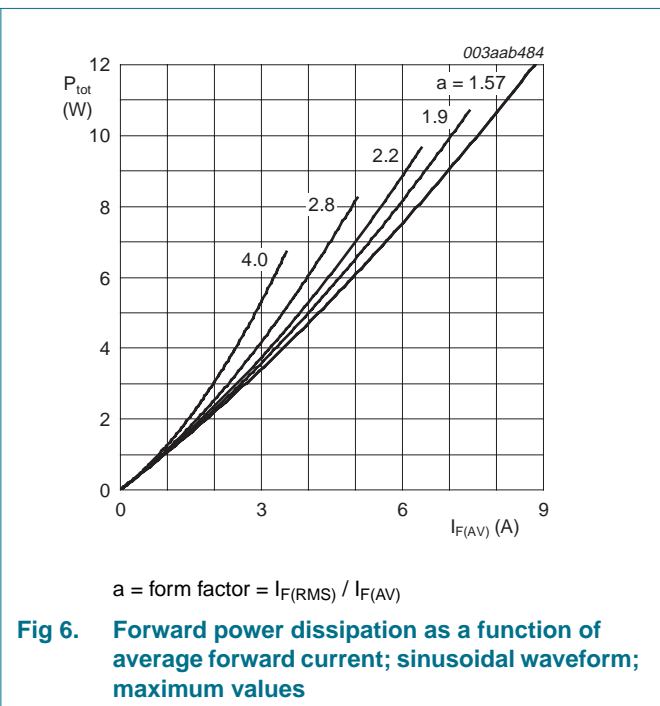
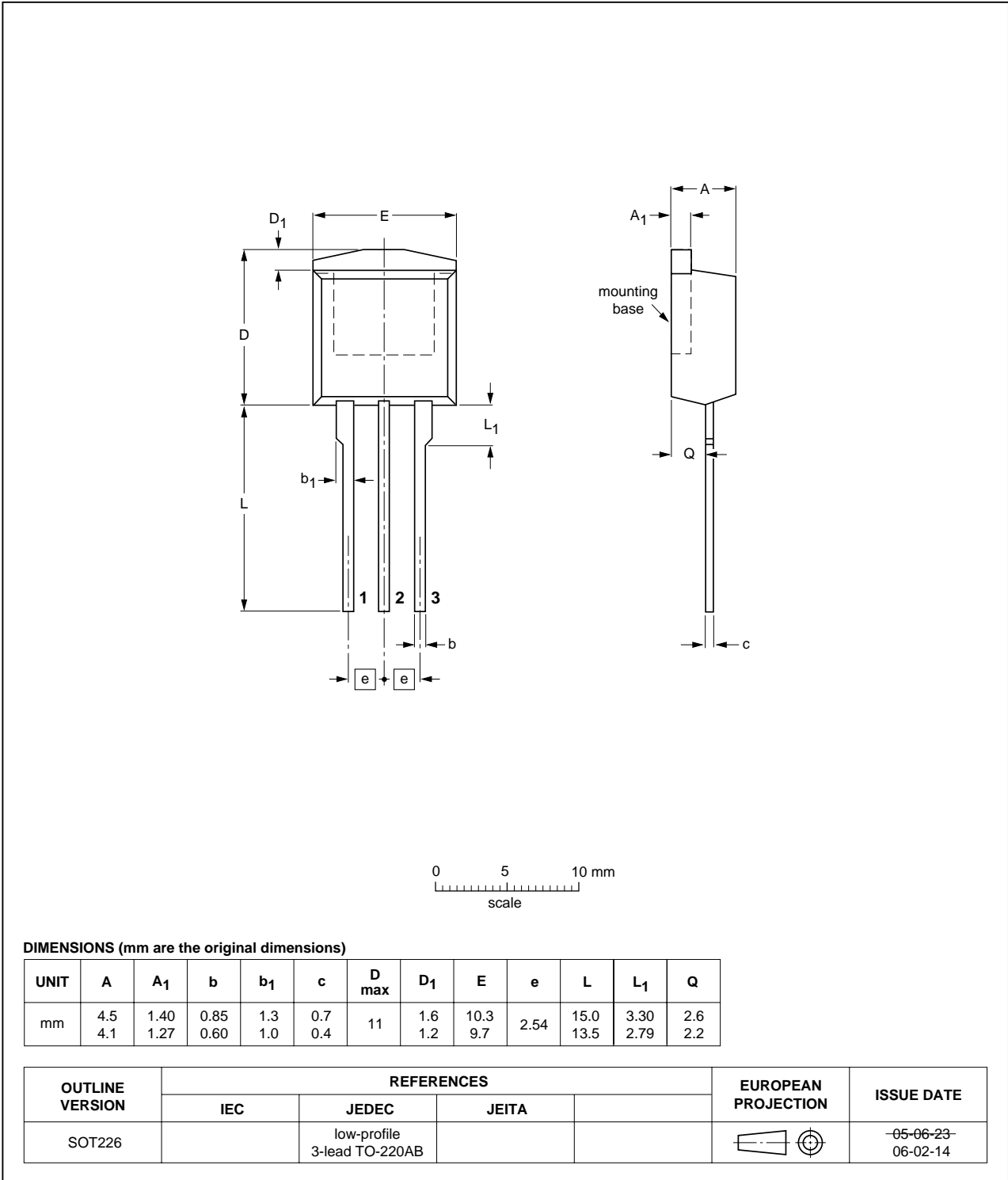


Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

**7. Package outline**

Plastic single-ended package (I2PAK); low-profile 3-lead TO-220AB

SOT226



**Fig 7. Package outline SOT226 (low-profile 3-lead TO-220AB)**

## 8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV34G-600_1	20090225	Product data sheet	-	-

## 9. Legal information

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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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